

## Quad 2-Line to 1-Line Data Selector/ Multiplexers with 3-State Outputs

The '257 and '258 multiplex, signals from four-bit data sources to four-output data lines in bus organized systems. The data presented at the outputs in non-inverted for the '257, and inverted for the '258.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

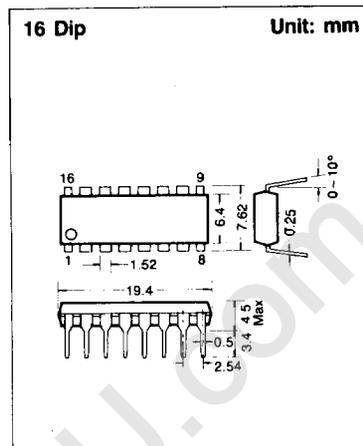
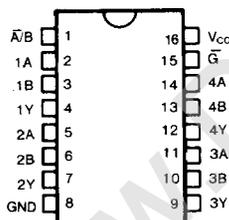
### FEATURES

- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current ( $I_{OL} = 24 \text{ mA} @ V_{OL} = 0.5V$ ) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:

KS74AHCT:  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$

KS54AHCT:  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$

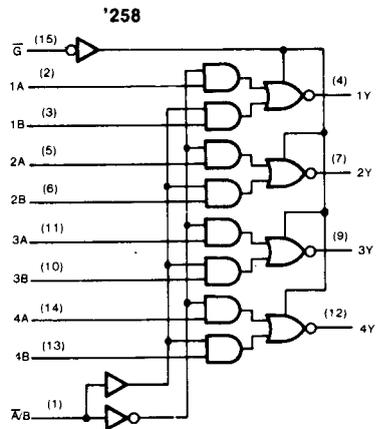
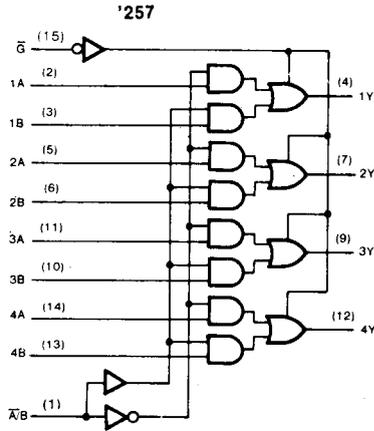
### PIN CONFIGURATION



### FUNCTION TABLE

Output Control $\bar{G}$	Inputs			Output Y	
	Select $\bar{A}/\bar{B}$	Data		'257	'258
		A	B		
H	X	X	X	Z	Z
L	L	L	X	L	H
L	L	H	X	H	L
L	H	X	L	L	H
L	H	X	H	H	L

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS\*

Characteristic	Symbol	Ratings	Unit
Supply Voltage Range	$V_{CC}$	-0.5 to +7.0	V
DC Input Diode Current ( $V_i < -0.5V$ or $V_i > V_{CC} + 0.5V$ )	$I_{ik}$	$\pm 20$	mA
DC Output Diode Current ( $V_o < -0.5V$ or $V_o > V_{CC} + 0.5V$ )	$I_{ok}$	$\pm 20$	mA
Continuous Output Current Per Pin ( $-0.5V < V_o < V_{CC} + 0.5V$ )	$I_o$	$\pm 70$	mA
Continuous Current Through $V_{CC}$ or GND pins		$\pm 250$	mA
Power Dissipation Per Package	$P_d^\dagger$	500	mW
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ C$

\* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:  
 Plastic Package (N): -12 mW/ $^\circ C$  from 65 $^\circ C$  to 85 $^\circ C$   
 Ceramic Package (J): -12 mW/ $^\circ C$  from 100 $^\circ C$  to 125 $^\circ C$

**RECOMMENDED OPERATING CONDITIONS**

Characteristic	Symbol	Value			Unit
		Min	Typ	Max	
Supply Voltage	V <sub>CC</sub>	4.5	5.0	5.5	V
DC Input & Output Voltages*	V <sub>IN</sub> , V <sub>OUT</sub>	0		V <sub>CC</sub>	V
Operating Temperature Range	KS74AHCT KS54AHCT T <sub>A</sub>	-40 -55		+85 +125	°C °C
Input Rise & Fall Times	t <sub>r</sub> , t <sub>f</sub>			500	ns

\* Unused inputs must always be tied to an appropriate logic voltage level (either V<sub>CC</sub> or GND)

**DC ELECTRICAL CHARACTERISTICS** (V<sub>CC</sub>=5V±10% Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	T <sub>A</sub> = 25°C		KS74AHCT	KS54AHCT	Unit
			Typ	Guaranteed Limits		T <sub>A</sub> = -40°C to +85°C	
Minimum High-Level Input Voltage	V <sub>IH</sub>			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V <sub>IL</sub>			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =-20μA I <sub>O</sub> =-6mA	V <sub>CC</sub> 4.2	V <sub>CC</sub> -0.1 3.98	V <sub>CC</sub> -0.1 3.84	V <sub>CC</sub> -0.1 3.7	V
Maximum Low-Level Output Voltage	V <sub>OL</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =20μA I <sub>O</sub> =12mA I <sub>O</sub> =24mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I <sub>IN</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND		±0.1	±1.0	±1.0	μA
Maximum 3-State Leakage Current	I <sub>oz</sub>	Output Enable = V <sub>IH</sub> V <sub>OUT</sub> =V <sub>CC</sub> or GND		±0.5	±5.0	±10.0	μA
Maximum Quiescent Supply Current	I <sub>CC</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>OUT</sub> =0μA		8.0	80.0	160.0	μA

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r, t_f \leq 2$  ns), AHCT257

Characteristic	Symbol	Conditions†	$T_A = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	KS74AHCT $T_A = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$	KS54AHCT $T_A = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$	Unit
			Typ	Guaranteed Limits		
Maximum Propagation Delay, A or B to any Y	$t_{PLH}$	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	7 13	11 20	13 24	ns
	$t_{PHL}$	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	7 13	11 20	13 24	
Maximum Propagation Delay, A/B to any Y	$t_{PLH}$	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	12 18	20 29	24 35	ns
	$t_{PHL}$	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	12 18	20 29	24 35	
Maximum Output Enable $\bar{G}$ to any Y	$t_{PZH}$	$R_L = 1\text{k}\Omega$ $C_L = 50\text{pF}$ $C_L = 150\text{pF}$	10 16	17 26	20 31	ns
	$t_{PZL}$		$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	10 16	17 26	
Maximum Output Disable Time, $\bar{G}$ to any Y	$t_{PHZ}$	$R_L = 1\text{k}\Omega$ $C_L = 50\text{pF}$	9	15	18	ns
	$t_{PLZ}$		9	15	18	
Maximum Input Capacitance	$C_{IN}$		5			pF
Maximum Output Capacitance	$C_{OUT}$	Output Disabled	10			pF
Power Dissipation Capacitance* (per mux)	$C_{PD}$	$\bar{G} = V_{CC}$	5			pF
		$\bar{G} = \text{GND}$	30			

\*  $C_{PD}$  determines the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

† For AC switching test circuits and timing waveforms see section 2.

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r, t_f \leq 2$  ns), AHCT258

Characteristic	Symbol	Conditions†	$T_A = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$	KS74AHCT $T_A = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$	KS54AHCT $T_A = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$	Unit
			Typ	Guaranteed Limits		
Maximum Propagation Delay, A or B to any Y	$t_{PLH}$	$C_L = 50\text{pF}$	6	10	12	ns
		$C_L = 150\text{pF}$	12	19	23	
	$t_{PHL}$	$C_L = 50\text{pF}$	6	10	12	
		$C_L = 150\text{pF}$	12	19	23	
Maximum Propagation Delay, A/B to any Y	$t_{PLH}$	$C_L = 50\text{pF}$	14	23	28	ns
		$C_L = 150\text{pF}$	20	32	39	
	$t_{PHL}$	$C_L = 50\text{pF}$	14	23	28	
		$C_L = 150\text{pF}$	20	32	39	
Maximum Output Enable Time, $\bar{G}$ to any Y	$t_{PZH}$	$C_L = 50\text{pF}$	11	18	22	ns
		$C_L = 150\text{pF}$	17	27	33	
	$t_{PZL}$	$R_L = 1\text{k}\Omega$				
		$C_L = 50\text{pF}$	11	18	22	
	$t_{PZL}$	$C_L = 150\text{pF}$	17	27	33	
Maximum Output Disable Time, $\bar{G}$ to any Y	$t_{PHZ}$	$R_L = 1\text{k}\Omega$	10	16	19	ns
		$C_L = 50\text{pF}$	10	16	19	
	$t_{PLZ}$					
Maximum Input Capacitance	$C_{IN}$		5			pF
Maximum Output Capacitance	$C_{OUT}$	Output Disabled	10			pF
Power Dissipation Capacitance* (per mux)	$C_{PD}$	$\bar{G} = V_{CC}$	5			pF
		$\bar{G} = \text{GND}$	30			

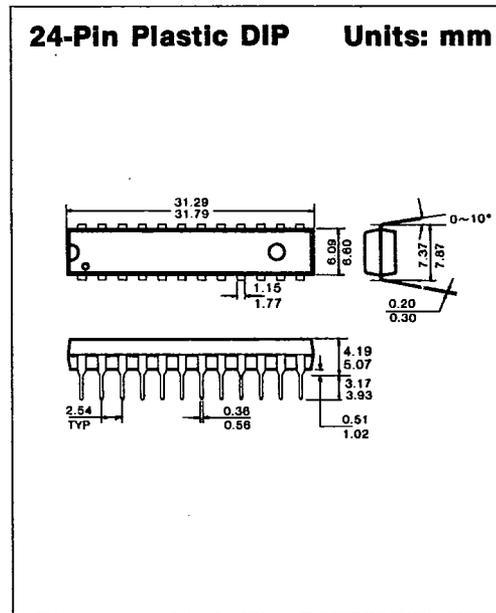
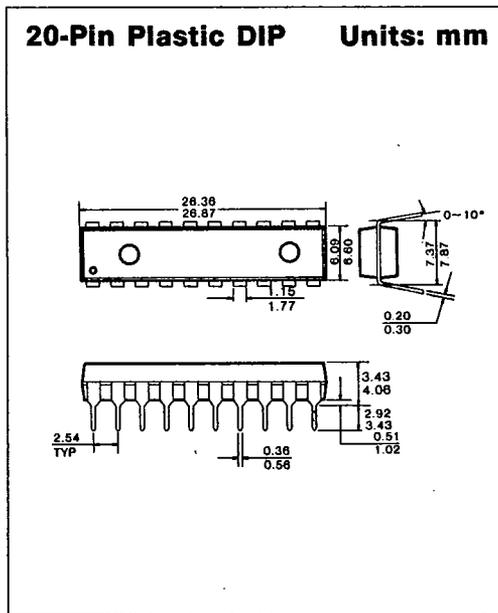
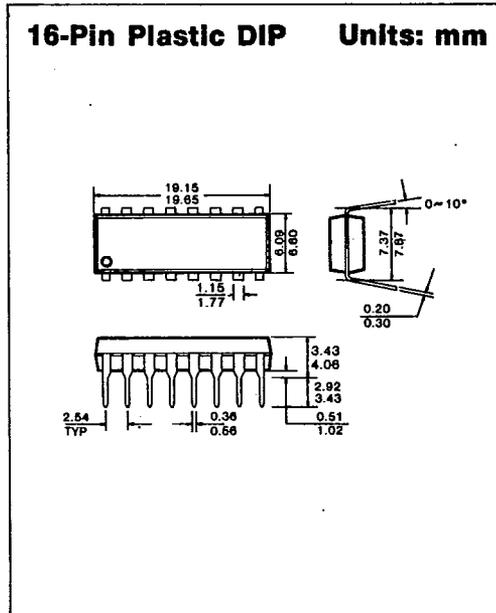
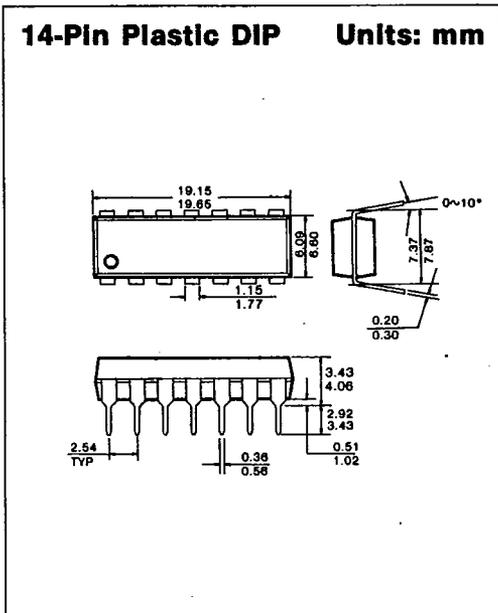
\*  $C_{PD}$  determines the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

† For AC switching test circuits and timing waveforms see section 2.

**PACKAGE DIMENSIONS**

T-90-20

**1. PLASTIC PACKAGES**

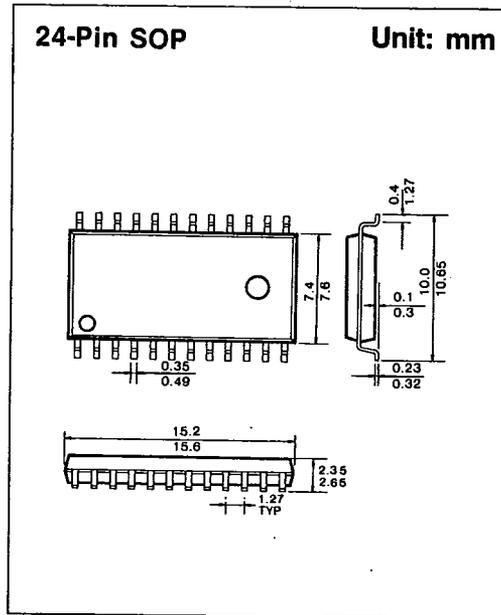
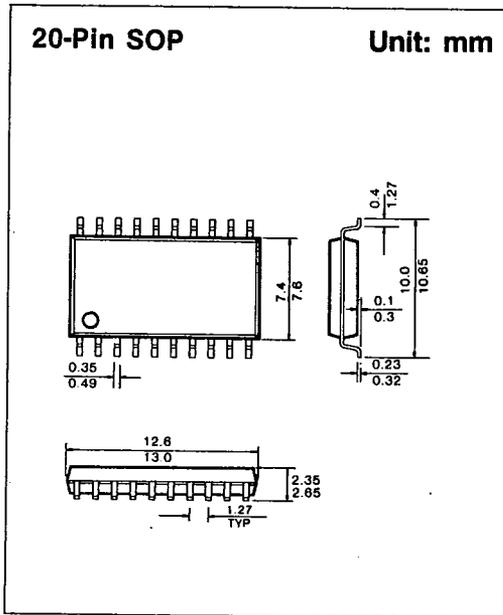
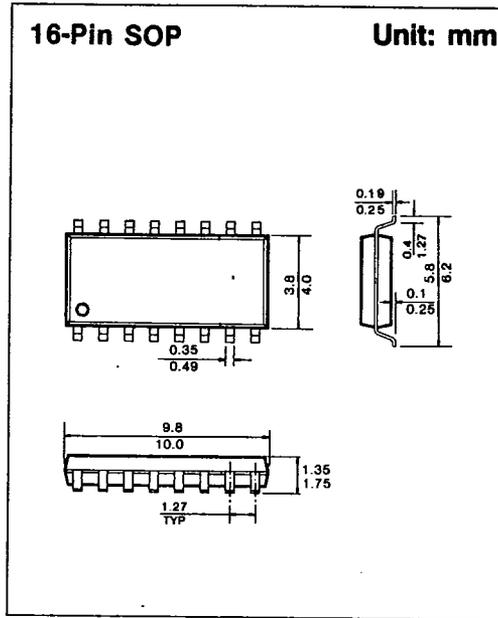
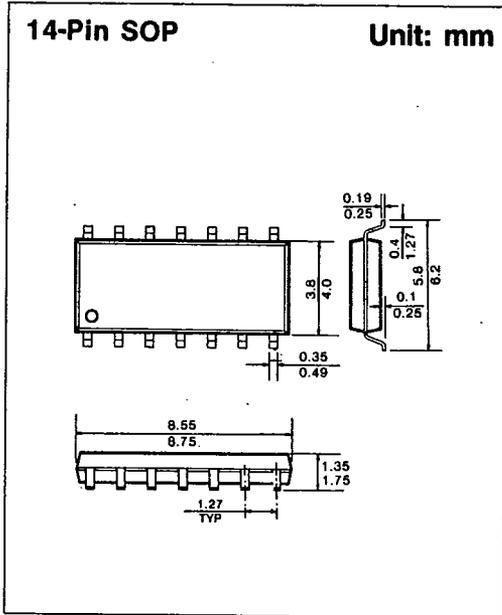


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**PACKAGE DIMENSIONS**

T-90-20

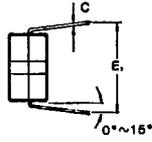
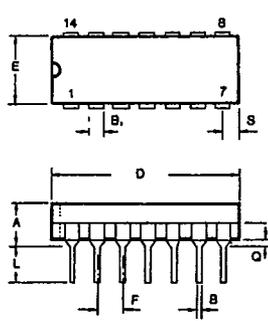


**PACKAGE DIMENSIONS**

T-90-20

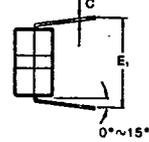
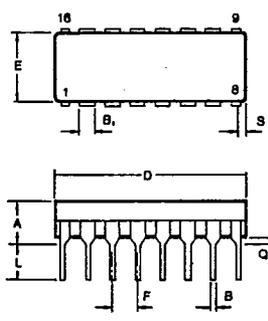
**2. CERAMIC PACKAGES**

**14-Pin Ceramic DIP Units: mm**



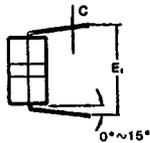
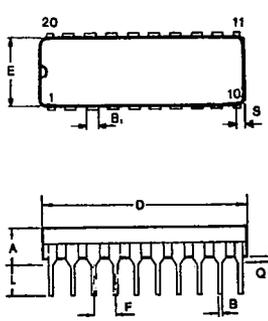
Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B1	1.40	1.78
C	0.20	0.38
D	18.16	19.58
E	8.10	7.49
E1	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	1.91	2.29

**16-Pin Ceramic DIP Units: mm**



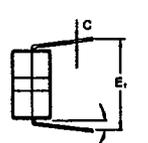
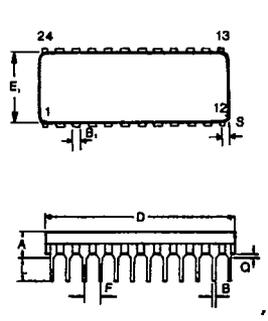
Dim	Millimeters	
	Min	Max
A	—	5.08
B	0.38	0.58
B1	1.40	1.78
C	0.20	0.38
D	19.05	19.94
E	8.10	7.49
E1	7.62	10.03
F	2.54	
L	3.18	4.19
Q	0.51	1.02
S	0.51	1.14

**20-Pin Ceramic DIP Units: mm**



Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B1	1.14	1.52
C	0.20	0.38
D	25.78	26.93
E	8.10	8.60
E1	7.77	7.88
F	2.54	
L	3.73	4.01
Q	0.38	0.89
S	0.51	1.14

**24-Pin Ceramic DIP Units: mm**



Dim	Millimeters	
	Min	Max
A	4.06	5.08
B	0.38	0.53
B1	1.14	1.52
C	0.20	0.38
D	31.50	32.84
E	7.24	7.75
E1	7.77	7.98
F	2.54	
L	3.73	4.01
Q	0.508	1.778
S	1.85	1.93

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SAMSUNG SEMICONDUCTOR

1677 A-06